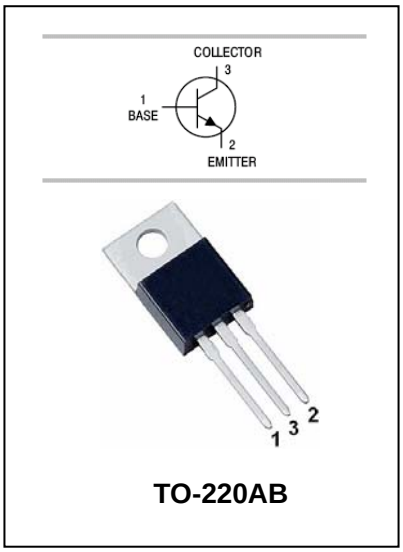
NPN Epitaxial Silicon Transistor 2SD880

FEATURES

- Low frequency power amplifier.
- Complememt to 2SB834.

Lead-free



TO-220AB

MAXIMUM RATING operating temperature range applies unless otherwise specified

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	60	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current Continuous	3	A
P_C	Collector Dissipation	1.5	W
T_j, T_{stg}	Junction and Storage Temperature	-55 to +150	℃

NPN Epitaxial Silicon Transistor 2SD880

ELECTRICAL CHARACTERISTICS Ratings at 25℃ ambient temperature unless otherwise specified.

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base Breakdown Voltage	$V_{(BR)CBO}$	I_C=100μA,I_E=0	60	-	-	V
Collector-emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=50mA,I_B=0	60	-	-	V
Emitter-base Breakdown Voltage	$V_{(BR)EBO}$	I_E=100μA,I_C=0	7	-	-	V
Collector Cut-off Current	I_{CBO}	V_{CB}=60V,I_E=0	-	-	100	μA
Emitter Cut-off Current	I_{EBO}	V_{EB}=7V,I_C=0	-	-	100	μA
DC Current Gain	h_{FE}	V_{CE}=5V,I_C=500mA	60	-	300	-
Collector-emitter Saturation Voltage	$V_{CE(sat)}$	I_C=3A, I_B=300mA	-	-	1	V
Base-emitter Voltage	V_{BE}	I_C=0.5A, V_{CE}=5V	-	-	1	V
Transition Frequency	f_T	V_{CE}=5V,I_C=500mA	-	3		MHz
Collector output capacitance	Cob	VCB=10V, IE=0, f=1MHz	-	70	-	pF
Turn-on Time	t_{on}	I_C=2A I_{B1}=-I_{B2}=200mA PW=20us	-	0.8	-	us
Storage Time	t_s		-	1.5	-	us
Fall Time	t_f		-	0.8	-	us

CLASSIFICATION OF h_{FE}

Range	O	Y	GR
Marking	60-120	100-200	150-300

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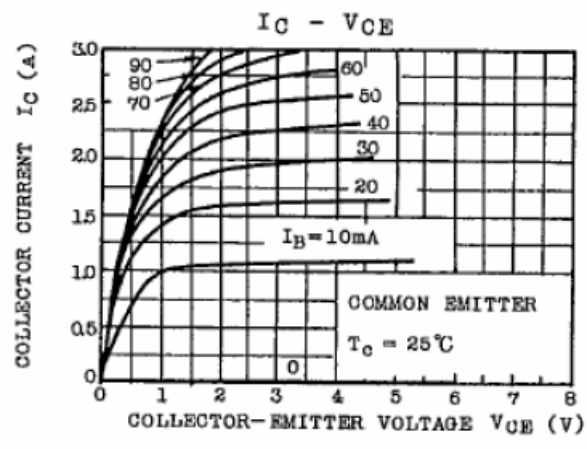
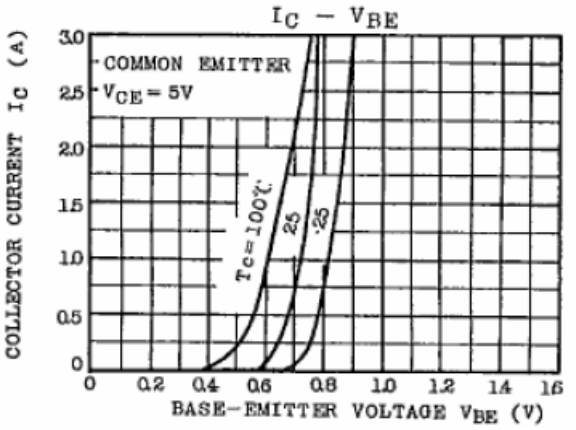
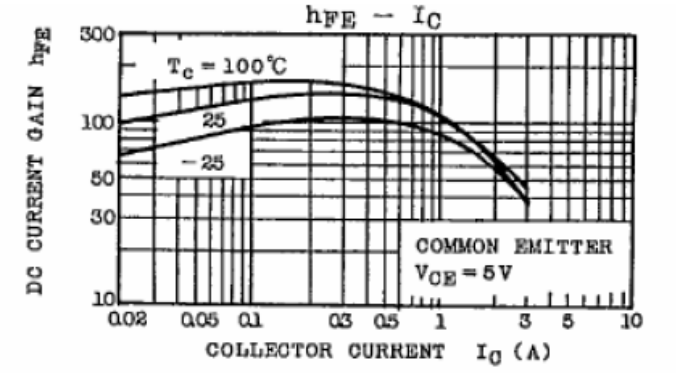
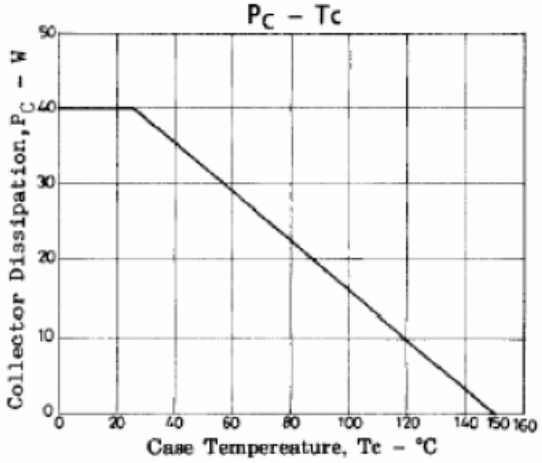
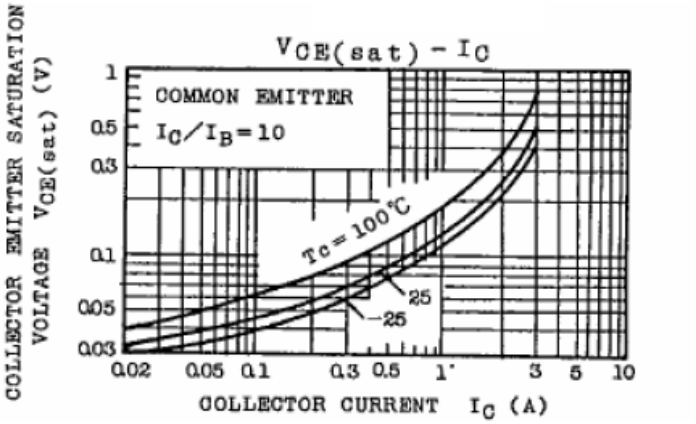
TYPICAL CHARACTERISTICS @ Ta=25℃ unless otherwise specified











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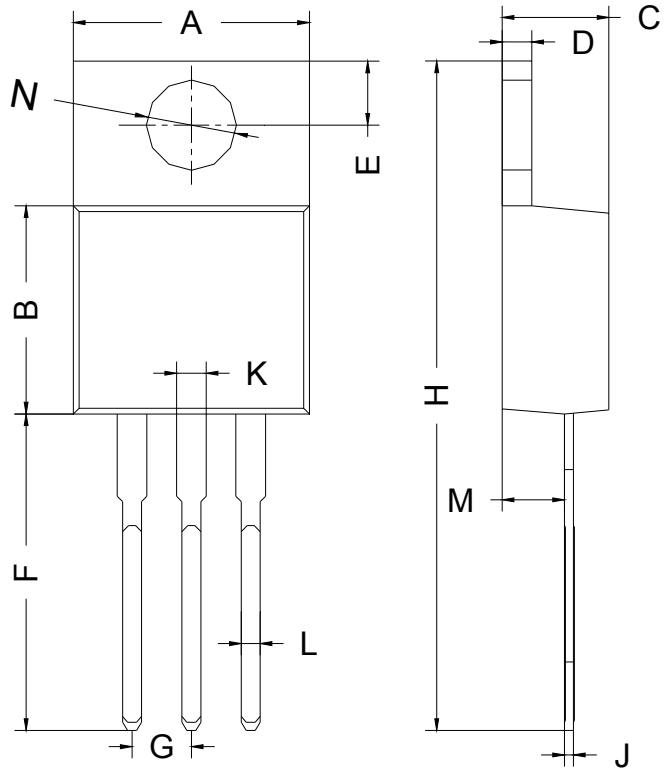
PACKAGE OUTLINE

Plastic surface mounted package TO-220AB



TO-220AB		
Dim	Min	Max
A	9.80	10.30
B	8.70	9.10
C	4.57 Typical	
D	1.27 Typical	
E	2.64	2.84
F	13.14	13.74
G	2.44	2.64
H	28.03	28.83
J	0.38 Typical	
K	1.22	1.32
L	0.71	0.91
M	2.50 Typical	
N	3.86 Typical	
All Dimensions in mm		